

2SB1320A

Silicon PNP epitaxial planer type

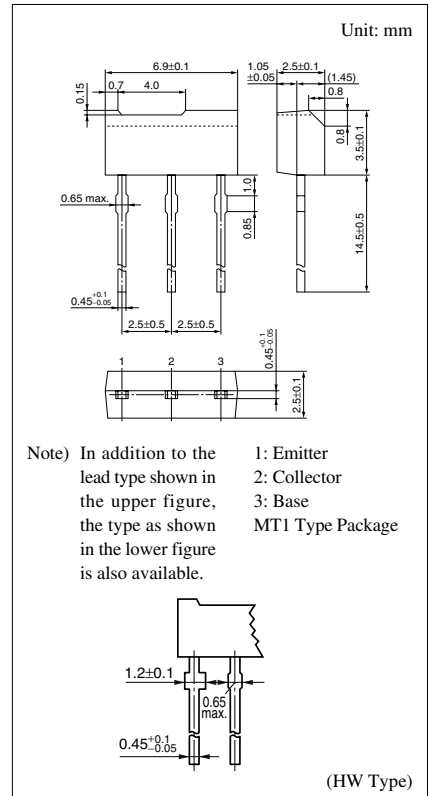
For general amplification
Complementary to 2SD1991A

■ Features

- High forward current transfer ratio h_{FE}
- Allowing supply with the radial taping

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-60	V
Collector to emitter voltage	V_{CEO}	-50	V
Emitter to base voltage	V_{EBO}	-7	V
Peak collector current	I_{CP}	-200	mA
Collector current	I_C	-100	mA
Collector power dissipation	P_C	400	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -20\text{ V}, I_E = 0$			-1	μA
	I_{CEO}	$V_{CE} = -20\text{ V}, I_B = 0$			-1	μA
Collector to base voltage	V_{CBO}	$I_C = -10\ \mu\text{A}, I_E = 0$	-60			V
Collector to emitter voltage	V_{CEO}	$I_C = -2\text{ mA}, I_B = 0$	-50			V
Emitter to base voltage	V_{EBO}	$I_E = -10\ \mu\text{A}, I_C = 0$	-7			V
Forward current transfer ratio *	h_{FE}	$V_{CE} = -10\text{ V}, I_C = -2\text{ mA}$	160		460	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{ mA}, I_B = -10\text{ mA}$			-1	V
Transition frequency	f_T	$V_{CB} = -10\text{ V}, I_E = 1\text{ mA}, f = 200\text{ MHz}$		80		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$		3.5		pF

Note) *: Rank classification

Rank	Q	R	S	No-rank
h_{FE}	160 to 260	210 to 340	290 to 460	160 to 460

Product of no-rank is not classified and have no indication for rank.

